

## ABSTRACT OF THE DISCLOSURE

A semiconductor laser device is formed by laminating optical confinement layers and active layers so as to  
5 dispose each of said active layers between said optical confinement layers, wherein one of the opposite ends perpendicular to the junction planes of the individual layers in the semiconductor multi-layer film is coated with a low reflection film and the other of the ends is coated  
10 with a high reflection film, wherein the low reflection film is an  $\text{Al}_2\text{O}_3$  film having a resistivity of  $1 \times 10^{12} \Omega \cdot \text{m}$  or more, preferably  $1 \times 10^{13} \Omega \cdot \text{m}$  or more, and having a stoichiometric ratio composition, which is deposited by, for example, an electron cyclotron resonance sputtering  
15 process. The present invention has realized a semiconductor laser device exhibiting a prolonged duration of operating life and having high driving reliability, which is advantageous in that a catastrophic optical damage hardly occurs and a lowering of the optical output after  
20 driving at a constant current is suppressed, and thus, it is preferably used as an optical transmitter for the optical communication.

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